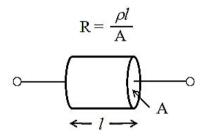


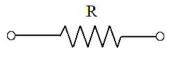
EE01205479 IoT for Electrical Engineering

Dr. Varodom Toochinda

#### Resistance



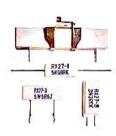
Physical



symbol

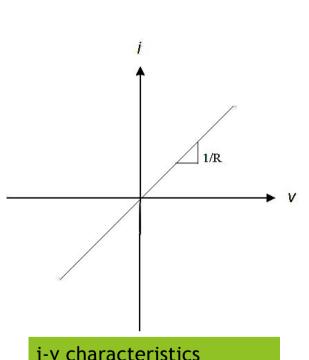






i-v characteristics

Resistors



#### **Basic Relationships**

Ohm's Law

$$V = IR$$

Power

$$P = VI = \frac{V^2}{R} = I^2 R$$



#### Kirchhoff's Current and Voltage Laws

► KCL

$$\sum_{n=1}^{N} i_n = 0$$

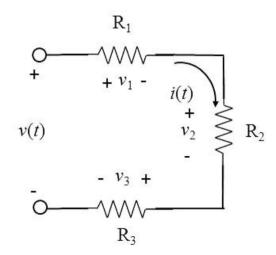
KVL

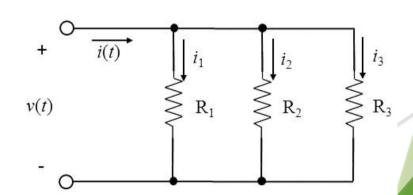
$$\sum_{n=1}^{N} v_n = 0$$



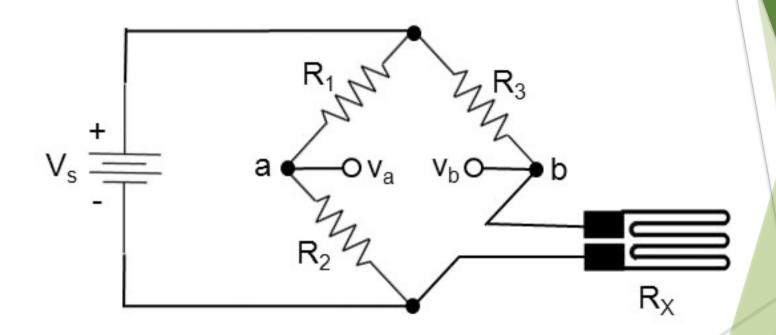
#### KCL and KVL applications

- Total resistance
  - Series
  - Parallel
- ► Current and voltage divider





#### Exercise1: Wheatstone bridge



Let Vs = 5 Volts. R1 = R2 = R3 = 1000 Ohms, Rx varies between 800 - 1200 Ohms. Compute the corresponding voltage range for Vab.

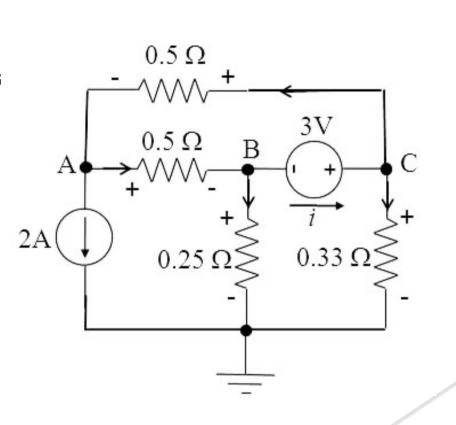
#### Circuit analysis methods

- Node voltage
- Mesh current
- Superposition
- Equivalent circuit/source transformation
  - ► Thevenin voltage source
  - Norton current source



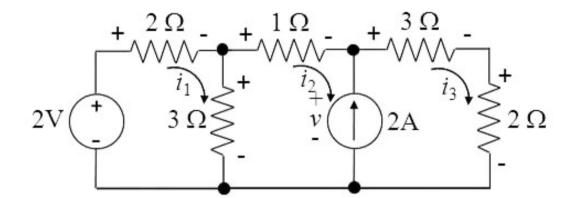
#### Node voltage analysis

- Assign  $V_A$ ,  $V_B$ ,  $V_C$  as variables
- Use KCL to solve

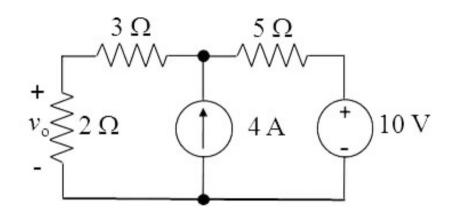


## Mesh current analysis

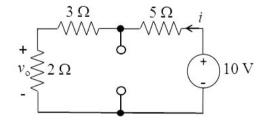
- $\blacktriangleright$  Assign  $i_1$ ,  $i_2$ ,  $i_3$  as variables
- Use KVL to solve

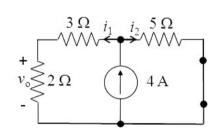


#### Superposition method



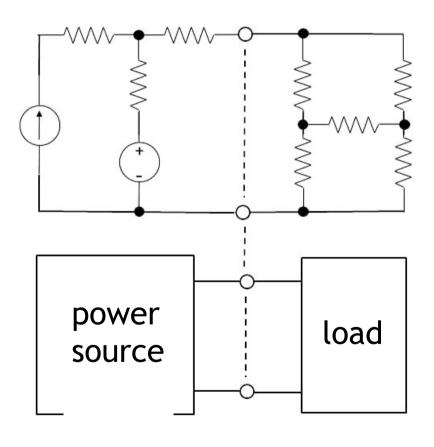
$$V_{o1} = (2/(2+3+5))*10 = 2 V$$
  
 $V_{o2} = 2*2 = 4 V$   
 $V_{o} = 2 + 4 = 6 V$ 

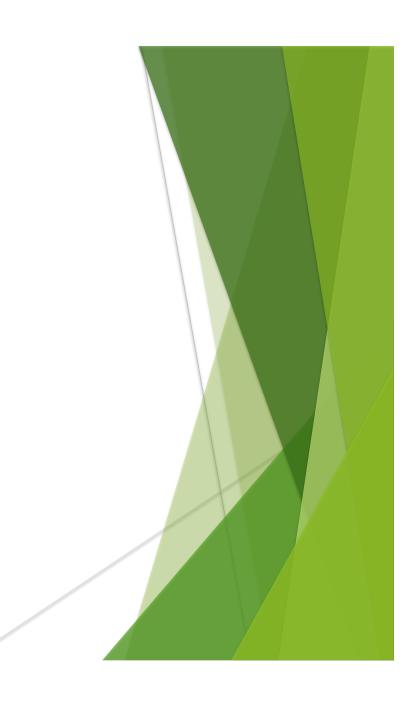




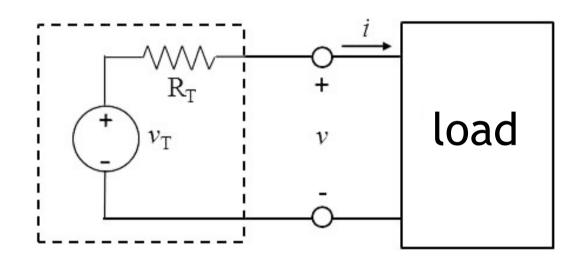


## Equivalent circuit concept



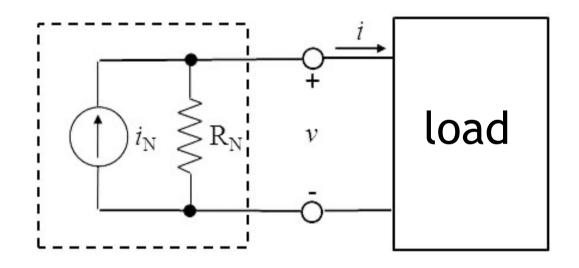


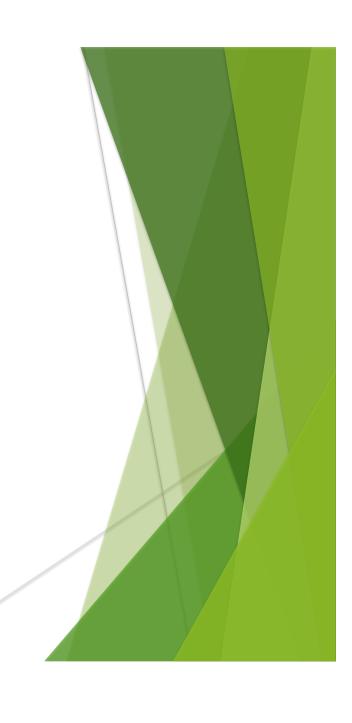
## Thevenin source



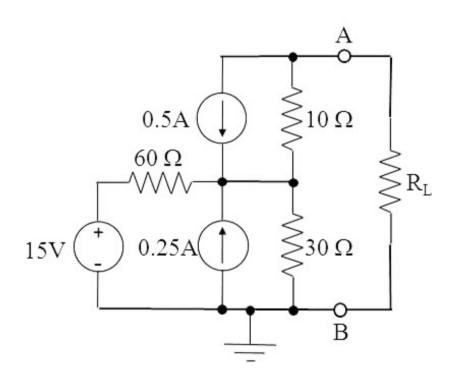


#### Norton source

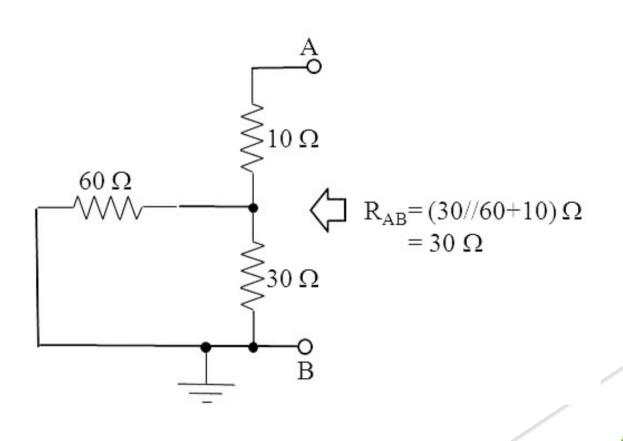


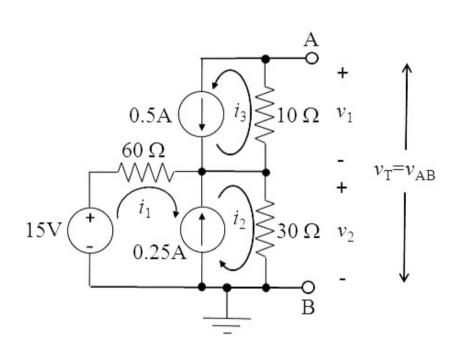


Example: Thevenin equivalent source



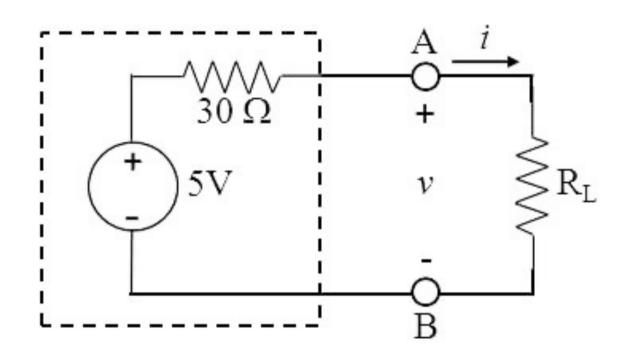
## Compute Thevenin resistance



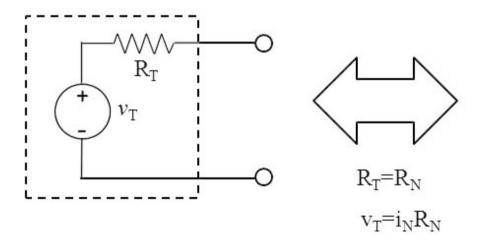


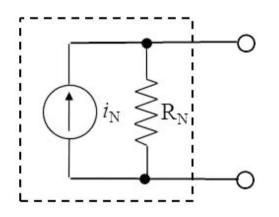
## Compute Thevenin voltage

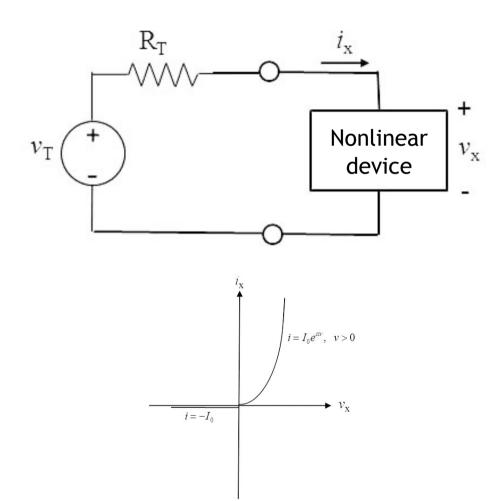
## Thevenin equivalent circuit



#### Source transformation



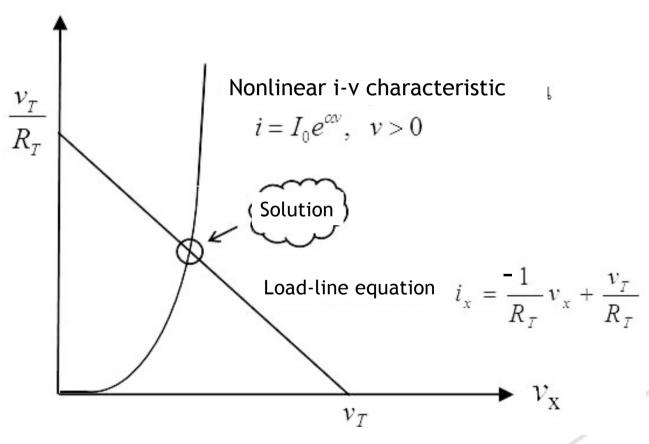


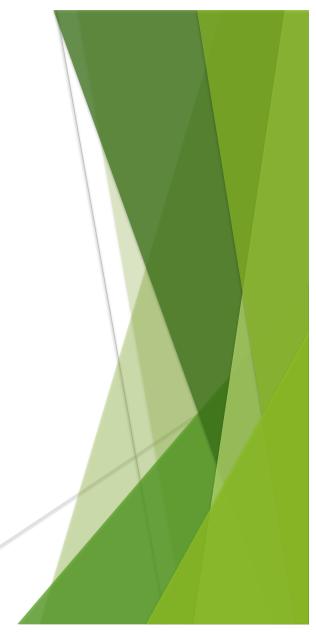


# Nonlinear load

- Load-line analysis
- Numerical method

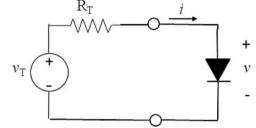
#### Load-line analysis





Exercise 2: Find current and voltage at diode by load-line and numerical methods

$$R_T=22\Omega$$
,  $V_T=12 V$ 

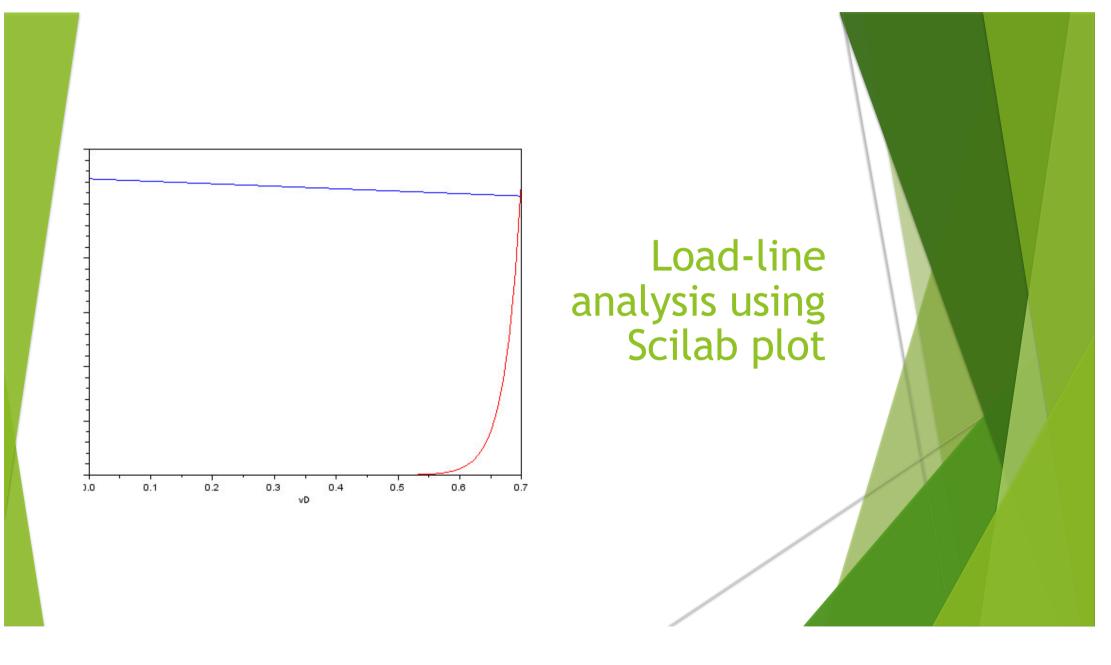


Diode i-v characteristic

$$i_D = I_{SAT} \left( \exp \left\{ \frac{v_D}{kT/q} \right\} - 1 \right)$$

at room temperature

$$I_{SAT} = 10^{-12} \text{ A}$$
  
 $\frac{kT}{q} = 0.0259 \text{ V}$ 



#### Flowchart of numerical method

